



NPN POWER DARLINGTON TRANSISTOR ARRAY

D76A3D

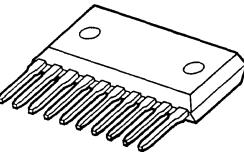
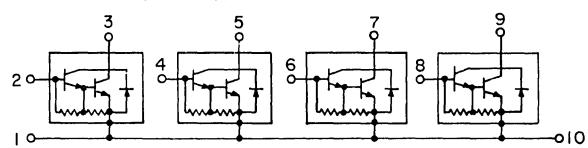
100 VOLTS
3 AMP, 4.0 WATTS

Designed for high power switching applications, hammer drive, pulse motor drive and inductive load drive applications.

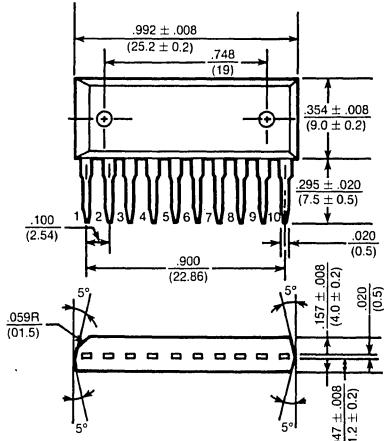
Features:

- High reliability small-sized available (4 in 1)
- Epoxy single-inline package (10 pin)
- High collector power dissipation: $P_D = 4W @ T_A = 25^\circ C$ (Four device action)
- High collector current: $I_C = 3A$ (Max.)
- High DC current gain: $h_{FE} = 2000$ (Min.) @ $V_{CE} = 2V$, $I_C = 1.5A$

ARRAY CONFIGURATION



CASE STYLE SIP-10 PIN
DIMENSIONS ARE IN INCHES AND (MILLIMETERS)



maximum ratings ($T_A = 25^\circ C$) (unless otherwise specified)

RATING	SYMBOL	D76A3D	UNITS
Collector-Emitter Voltage	V_{CEO}	100	Volts
Collector-Base Voltage	V_{CBO}	120	Volts
Emitter Base Voltage	V_{EBO}	6	Volts
Collector Current — Continuous Peak	I_C I_{CM}	3 6	A
Base Current — Continuous	I_B	0.5	A
Collector Power Dissipation (One Device Action, $T_A = 25^\circ C$)	P_D	2.0	Watts
Collector Power Dissipation (Four Device Action, $T_A = 25^\circ C$)	P_D	4.0	Watts
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to +150	°C

thermal characteristics

Thermal Resistance, Junction to Ambient (Four Device Action)	$\Sigma R_{\theta JA}$	31.3	°C/W
Maximum Lead Temperature for Soldering Purpose: $\frac{1}{8}$ " from Case for 5 Seconds	T_L	260	°C

electrical characteristics ($T_A = 25^\circ C$) (unless otherwise specified)

CHARACTERISTIC	SYMBOL	MIN	TYP	MAX	UNIT
off characteristics					
Collector-Emitter Breakdown Voltage ($I_C = 10mA$, $I_B = 0$)	$V_{BR(CEO)}$	100	—	—	Volts
Collector-Base Breakdown Voltage ($I_C = 1mA$, $I_E = 0$)	$V_{BR(CBO)}$	120	—	—	Volts
Collector Cutoff Current ($V_{CB} = 120V$, $I_E = 0$)	I_{CBO}	—	—	10	μA
Collector Cutoff Current ($V_{CE} = 100V$, $I_B = 0$)	I_{CEO}	—	—	10	μA
Emitter Cutoff Current ($V_{EB} = 6V$, $I_C = 0$)	I_{EBO}	—	—	2.5	mA

on characteristics

DC Current Gain ($I_C = 1.5A$, $V_{CE} = 2V$) ($I_C = 3A$, $V_{CE} = 2V$)	h_{FE}	2000 1000	—	12000	—
Collector-Emitter Saturation Voltage ($I_C = 1.5A$, $I_B = 3mA$)	$V_{CE(sat)}$	—	—	1.5	Volts
Base-Emitter Saturation Voltage ($I_C = 1.5A$, $I_B = 3mA$)	$V_{BE(sat)}$	—	—	2.0	Volts

switching characteristics

Turn-on Time	$V_{CC} = 30V$ $I_{B1} = -I_{B2} = 3mA$ Duty Cycle = 1%	t_{on}	—	0.3	—	μs
Storage Time		t_{stg}	—	2	—	
Fall Time		t_f	—	0.4	—	

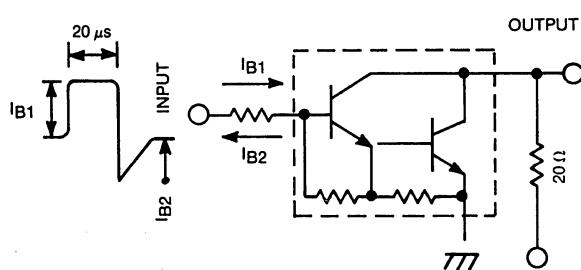


FIG. 1. SWITCHING TIME TEST CIRCUIT

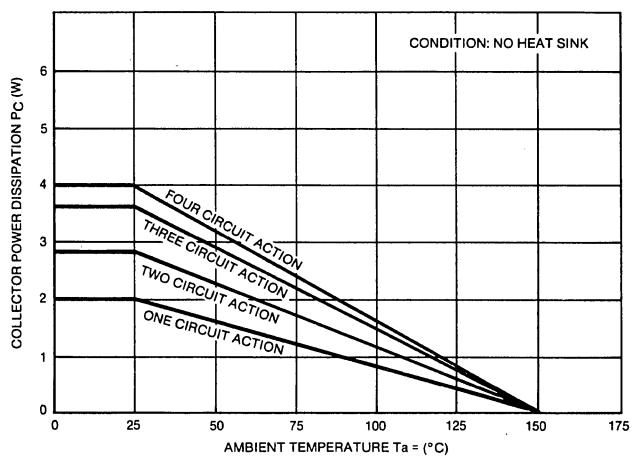


FIG. 2. TOTAL COLLECTOR POWER DISSIPATION